



## Claims

1. A transistor comprising elements of bipolar static induction transistors: two gates, four sources, channels and six electrodes on either side of a lightly doped n-type silicon monocrystal substrate;

one of said channels of the multielement structures is thicker than the other channels on either side of said substrate;

said thick channels are connected to the separate electrodes on either side of said substrate.

2. The transistor according to claim 1 wherein an impurity concentration near the gate is high enough.

3. The transistor according to claim 2 wherein an epitaxial layers of the same type of conductivity with the impurity concentration of about  $10^{17} \text{ cm}^{-3}$  are disposed on either side of said substrate;

said gates, said sources and said channels are disposed in said epitaxial layers.

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## Claims

1. "canceled".

2. "three times amended". A transistor comprising elements of (a) bipolar static induction transistors: (a) two gates, (a) four sources, (and a) channels and six electrodes on (each of the) either side(s) of a lightly doped n-type silicon monocrystal substrate;

one of said (the) channels of the multielement structures (on each of the sides of the substrate) is thicker than the other channels on either side of said substrate;

(this) said thick channels (is) are connected to (a) the separate electrodes on either side of said substrate.

2a. The transistor according to claim 2 wherein an impurity concentration near the gate is high enough.

3. "four times amended". The transistor according to claim 2a wherein (comprising on each of the sides of a lightly doped substrate) an epitaxial layers of the same type of conductivity with the impurity concentration of about  $10^{17}$  cm.<sup>sup.</sup>-3 are disposed on either side of said substrate;

(in which elements of a bipolar static induction transistor:); (a) said gates, (a) said sources and (a) said channels are disposed in said epitaxial layers.

4. "canceled".

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